

ST 2SC2655 (TO-92)

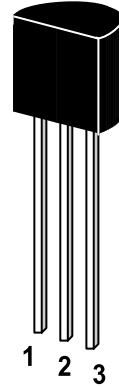
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NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into two groups O and Y, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.

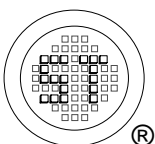


1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a=25^{\circ}\text{C}$)

| | Symbol | Value | Unit |
|---------------------------|------------------|-------------|--------------------|
| Collector Base Voltage | V_{CBO} | 50 | V |
| Collector Emitter Voltage | V_{CEO} | 50 | V |
| Emitter Base Voltage | V_{EBO} | 5 | V |
| Collector Current | I_{C} | 2 | A |
| Power Dissipation | P_{tot} | 900 | mW |
| Junction Temperature | T_{j} | 150 | $^{\circ}\text{C}$ |
| Storage Temperature Range | T_{s} | -55 to +150 | $^{\circ}\text{C}$ |



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
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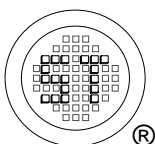
Dated : 07/12/2002

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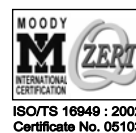
Characteristics at $T_{amb}=25^{\circ}\text{C}$

| | Symbol | Min. | Typ. | Max. | Unit | |
|------------------------------------------------------------------------|---------------|----------|------|------|---------------|---|
| DC Current Gain at $V_{CE}=2\text{V}$, $I_C=0.5\text{A}$ | O | h_{FE} | 70 | - | 140 | - |
| | Y | h_{FE} | 120 | - | 240 | - |
| | | h_{FE} | 40 | - | - | - |
| Collector Base Breakdown Voltage at $I_C=1\text{mA}$ | $V_{(BR)CBO}$ | 50 | - | - | V | |
| Collector Emitter Breakdown Voltage at $I_C=10\text{mA}$ | $V_{(BR)CEO}$ | 50 | - | - | V | |
| Emitter Base Breakdown Voltage at $I_E=1\text{mA}$ | $V_{(BR)EBO}$ | 5 | - | - | V | |
| Collector Cutoff Current at $V_{CB}=50\text{V}$ | I_{CBO} | - | - | 1 | μA | |
| Emitter Cutoff Current at $V_{EB}=5\text{V}$ | I_{EBO} | - | - | 1 | μA | |
| Collector Saturation Voltage at $I_C=1\text{A}$, $I_B=50\text{mA}$ | $V_{CE(sat)}$ | - | - | 0.5 | V | |
| Base Saturation Voltage at $I_C=1\text{A}$, $I_B=50\text{mA}$ | $V_{BE(sat)}$ | - | - | 1.2 | V | |
| Gain Bandwidth Product at $V_{CE}=2\text{V}$, $I_C=0.5\text{A}$ | f_T | - | 100 | - | MHz | |
| Output Capacitance at $V_{CB}=10\text{V}$, $f=1\text{MHz}$ | C_{OB} | - | 40 | - | pF | |



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